



BCL65S10D3

Silicon Carbide Schottky Diode

650V, 10A

Description

BCL65S10D3 utilizes Bestirpower's advanced silicon carbide diode technology. This technology combines the benefits of excellent low forward voltage and robustness. Consequently, the family is suitable for application requiring high power efficiency

Benefits

- System efficiency improvement over Si diodes
- Low heat dissipation requirements
- Reduce size and cost of the system
- High-reliability

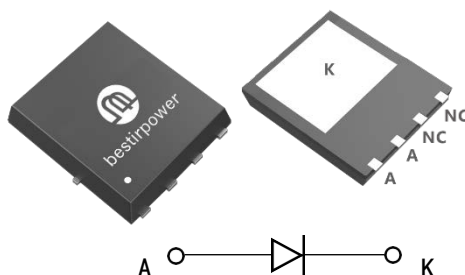
Applications

- Switch mode power supply
- Power factor correction
- Data Center
- Uninterruptible power supply

Features

V_{RRM}	I_F	T_C	Q_c
650 V	10 A	148 °C	28 nC

- Negligible reverse recovery
- High-speed switching
- Temperature independent switching behavior
- Higher frequency
- RoHS compliant / Halogen-free



Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		650	V
I_F	Forward Current	$T_C = 25^\circ\text{C}$	27	A
		$T_C = 124^\circ\text{C}$	19	A
		$T_C = 148^\circ\text{C}$	10	A
$I_{F,SM}$	Non-Repetitive Forward Surge Current	$T_C = 25^\circ\text{C}, t_p = 10 \text{ ms}$	126	A
		$T_C = 110^\circ\text{C}, t_p = 10 \text{ ms}$	80	A
$I_{F,RM}$	Repetitive Peak Forward Surge Current	$T_C = 25^\circ\text{C}, t_p = 10 \text{ ms}$	55	A
		$T_C = 110^\circ\text{C}, t_p = 10 \text{ ms}$	45	A
I^2dt value	$\int I^2 dt$	$T_C = 25^\circ\text{C}, t_p = 10 \text{ ms}$	20	A^2S
		$T_C = 110^\circ\text{C}, t_p = 10 \text{ ms}$	15	A^2S
P_{tot}	Power Dissipation	$T_C = 25^\circ\text{C}$	97	W
		$T_C = 110^\circ\text{C}$	42	W
		$T_C = 150^\circ\text{C}$	16	W
T_J, T_{STG}	Operating Junction and Storage Temperature		-55 to +175	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Typ.	1.54	$^{\circ}C/W$

Electrical Characteristics ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{DC}	DC blocking voltage		650			V
V_F	Forward Voltage	$I_F=10A, T_J=25^{\circ}C$	-	1.45	1.7	V
		$I_F=10A, T_J=175^{\circ}C$	-	1.75	2.0	
I_R	Reverse Current	$V_R = 650 V, T_J = 25^{\circ}C$	-	2	20	μA
		$V_R = 650 V, T_J = 175^{\circ}C$	-	40	200	
Q_C	Total Capacitive Charge	$V_R = 400 V, T_J = 25^{\circ}C$	-	28	-	nC
C	Total Capacitance	$V_R = 0 V, f = 1MHz$	-	550	-	pF
		$V_R = 200 V, f = 1MHz$	-	53	-	
		$V_R = 400 V, f = 1MHz$	-	48	-	
E_C	Capacitance Stored Energy	$V_R = 400 V, T_C = 25^{\circ}C$	-	7.0	-	μJ

Typical Performance Characteristics

Figure 1. Forward Characteristics

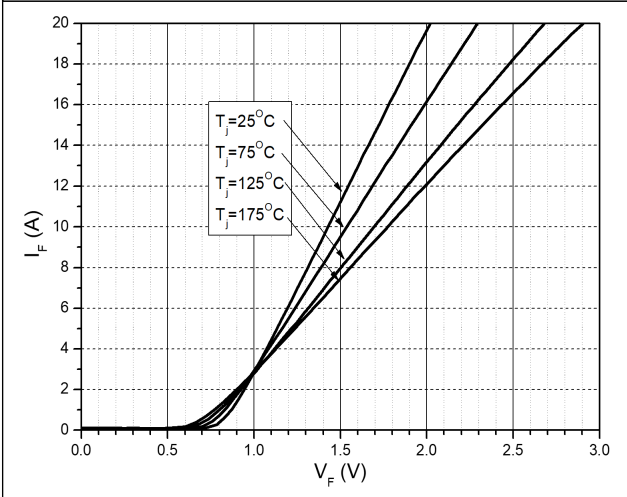


Figure 2. Reverse Characteristics

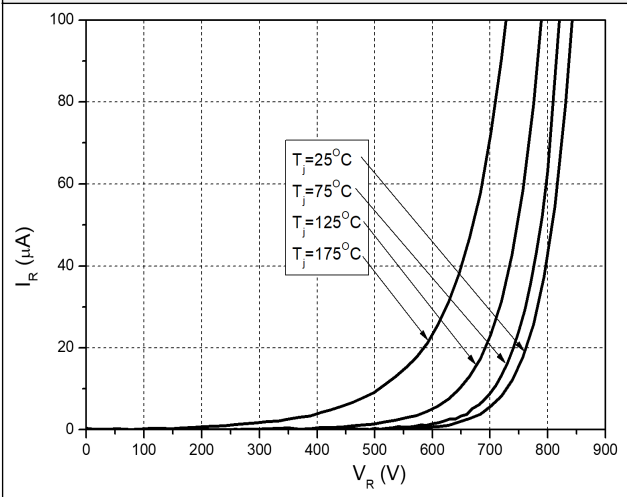


Figure 3. Capacitance vs. Reverse Voltage

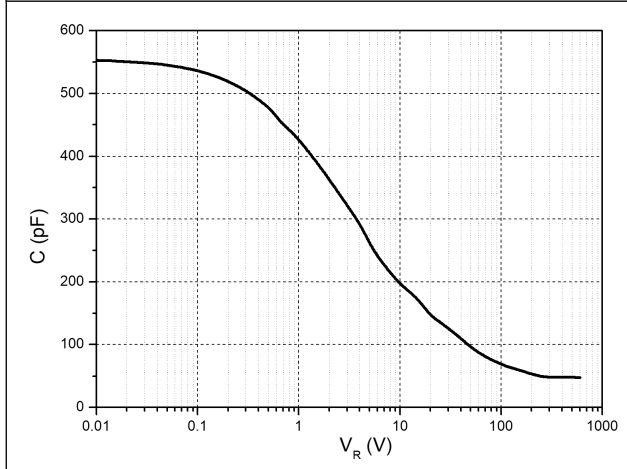
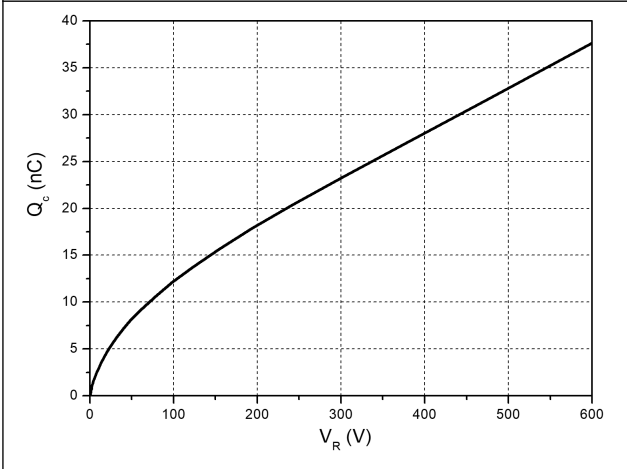
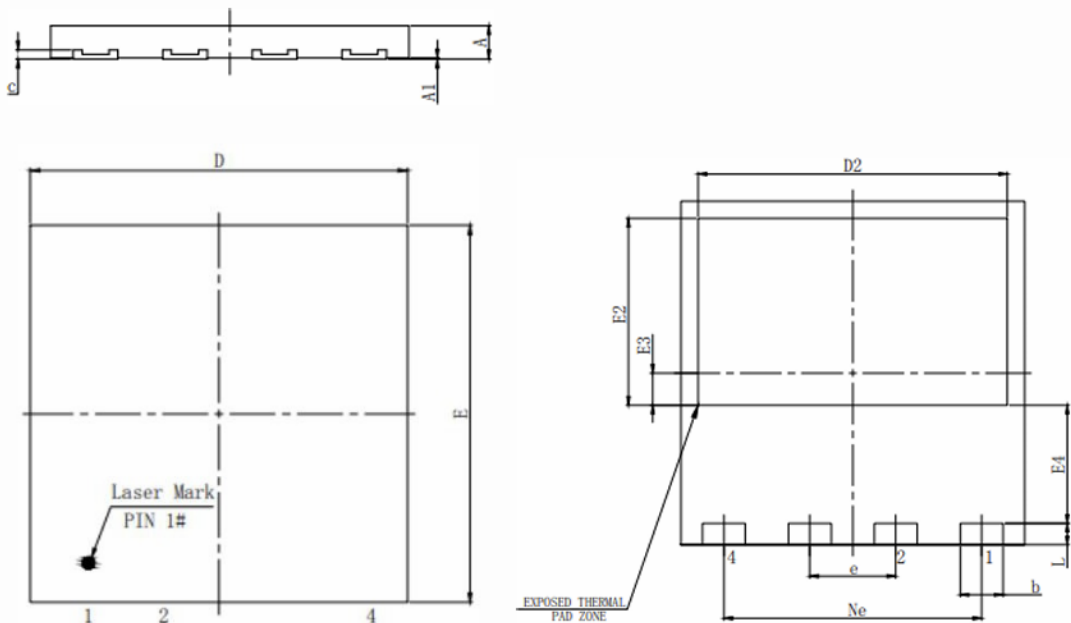


Figure 4. Capacitance Charge vs. Reverse Voltage



Package Outlines

DFN 8*8



Symbol	Dimensions In Millimeters		
	Min	Nom	Max
D	7.90	8.00	8.10
E	7.90	8.00	8.10
D2	7.10	7.20	7.30
E2	4.25	4.35	4.45
e	2.00BSC		
E3	0.75REF		
E4	2.75REF		
Ne	6.00BSC		
b	0.95	1.00	1.05
A	0.70	0.75	0.80
c	0.203REF		
A1	0	/	0.050
L	0.40	0.50	0.55

Package Marking and Ordering Information

Part Number	Top Marking	Package	Packing Method	Quantity
BCL65S10D3	BCL65S10D3	DFN8*8	Tape & Reel	5000 units

Disclaimer

Bestirpower reserve the right to make changes, corrections, enhancements, modifications, and improvements to Bestirpower products and/or to this document at any time without notice.

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. Bestirpower does not assume any liability for infringement of patents, copyrights, or other intellectual property rights of third parties by or arising from the use of Products or technical information described in this document.

This document is the property of Bestirpower Co., LTD., and not allowed to copy or transformed to other format if not under the authority approval.

© 2024 bestirpower – All rights reserved